

## REMARKS

The title and abstract have been revised to correspond more closely to the pending claims, all of which are method claims.

37 CFR 1.121 does not appear to prescribe how the title and abstract of a U.S. patent application are to be amended. Accordingly, Applicant's Attorney has used a reasonable technique for amending the title and abstract of the present application. In particular, Applicant's Attorney has used the same technique for amending the title and abstract as is prescribed in 37 CFR 1.121 for amending the specification of a U.S. patent application, namely that new material is underlined and deleted material is struck through.

The specification has been revised to correct various self-evident errors in spelling, typing, punctuation, reference-symbol usage, figure identification, and singular-versus-plural case. The missing verb "operates" has been inserted into the first sentence of paragraph 110, pages 25 and 26. The missing reference symbol "164" has been inserted between "162" and "166" in the first sentence of paragraph 146, pages 37 and 38, so that the corrected recitation "162, 164, 166" conforms to the later recitation "112, 114, 116" in that sentence.

The term "junction depletion 118" in paragraph 155, page 40, of the specification has been corrected to "junction depletion region 118" in conformity with usage of the term "junction depletion region 118" elsewhere in the specification. In paragraph 167, page 45, "threshold values  $V_X$ " has been corrected to "transition values  $V_X$ " since "value  $V_X$ " or "values  $V_X$ " is preceded by the word "transition" elsewhere in the specification, e.g., in the last sentence of paragraph 167.

The second sentence of paragraph 194, page 53, originally recited that "If electrode portions 112LA and 112LB are both n-type and thus of opposite conductivity type to body region 100, electrode portion 112LA is doped more lightly n-type than is electrode portion 112LB". The third (next) sentence of paragraph 194 then recites that "In accordance with Eq. 33, gate portion 131B meets the requirement of having a higher value of zero-point gate-to-body threshold voltage  $V_{T0}$  than gate portion 131A".

Contrary to what was originally stated in the third sentence of paragraph 194, application of Eq. 33 (paragraph 165, page 44) to the situation in which electrode portions 112LA and 112LB are both n-type and thus of opposite conductivity type to p-type body region 100 actually leads to the requirement that electrode portion 112LA be doped more

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heavily, rather than more lightly, than electrode portion 112LB in order for gate portion 131B to be of higher zero-point gate-to-body threshold voltage  $V_{T0}$  than gate portion 131A. Consequently, the second sentence of paragraph 194 has been corrected to recite that "If electrode portions 112LA and 112LB are both n-type and thus of opposite conductivity type to body region 100, electrode portion 112LA is doped more heavily n-type than is electrode portion 112LB". This correction is further supported by the third sentence of paragraph 195 (the next paragraph), page 53, that "If gate electrode layer 112L or 162L is divided into multiple portions of opposite conductivity type to body region 100 or 150 and of different  $N_{POLY}$  values, each gate electrode portion extends over part of plate region 100 or 152 or/and is continuous with another such gate electrode portion more heavily [emphasis added] doped than that gate electrode portion".

The fourth sentence of paragraph 194 recites that "The reverse dopant-concentration relationship arises if electrode portions 112LA and 112LB are both p-type and thus of the same conductivity type as body region 100". The fifth (next) sentence of paragraph 194 originally recited that "Per Eq. 33, electrode portion 112LA is doped more heavily p-type than is electrode portion 112LB".

Similar to what was stated above about the opposite conductivity-type situation in regard to the second and third sentences of paragraph 194 and contrary to what was originally stated in the fifth sentence of paragraph 194, application of Eq. 33 to the situation in which electrode portions 112LA and 112LB are both p-type and thus of the same conductivity type as p-type body region 100 leads to the requirement that electrode portion 112LA be doped more lightly, rather than more heavily, than electrode portion 112LB in order for gate portion 131B to be of higher zero-point gate-to-body threshold voltage  $V_{T0}$  than gate portion 131A. The fifth sentence of paragraph 194 has therefore been corrected to recite that "Per Eq. 33, electrode portion 112LA is doped more lightly p-type than is electrode portion 112LB". This correction to paragraph 194 is further supported by the fourth sentence of paragraph 195 (again the next paragraph) that "If electrode layer 112L or 162L is divided into multiple portions of the same conductivity type as body region 100 or 150 and of different  $N_{POLY}$  values, each gate electrode portion extends over part of plate region 102 or 152 or/and is continuous with another such gate electrode portion more lightly [emphasis added] doped than that gate electrode portion".

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The terms "more lightly doped" and "more heavily doped" in paragraph 196, pages 53 and 54, of the specification have been respectively corrected to "more heavily doped" and "more lightly doped" for the reasons given in the previous four paragraphs.

For the case in which level shifter 234 is present, the last sentence of paragraph 268, page 73, originally specified that "The length of the  $V_{Rmin}$ -to- $V_{Rmax}$  range is  $V_{HH} - V_{LL} - V_{LS}$ , the same as arises when shifter 234 is absent". However, paragraph 266, also page 73, specifies that the length of the  $V_{Rmin}$ -to- $V_{Rmax}$  range is  $V_{HH} - V_{LL} - V_{GBi}$  when shifter 234 is absent. Consequently, the last sentence of paragraph 268 has been corrected to recite "The length of the  $V_{Rmin}$ -to- $V_{Rmax}$  range is  $V_{HH} - V_{LL} - V_{GBi}$ , the same as arises when shifter 234 is absent".

In paragraph 272, page 74, "plate electrode 162" has been changed to "gate electrode 162" since item 162 is the gate electrode. Finally, paragraph 317, page 86, has been revised to identify the U.S. patent number for the additional patent application cited in that paragraph.

Turning to the claims, a grammatical error has been corrected in Claim 1. Claims 67 and 68 have been revised to make it clear that the recited semiconductor material includes dopant by variously inserting "doped" before "semiconductor material".

Claims 69 - 128 have been added to claim the invention with more particularity. New Claims 83, 89, 95, 107, and 117 are independent claims. The remaining new claims are dependent claims. Claims 61 - 128 are now pending.

The application is ready for examination.

Please telephone Applicant's Attorney at 650-964-9767 if there are any questions.

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Respectfully submitted,

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